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PTO/SB/66 (09-04)
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U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

STATEMENT UNDER 37 CFR 3.73(b)

Applicant/Patent Owner: Grandis, Inc.

Application No./Patent No.: See Attached Schedule Filed/Issue Date: See Attached Schedule

Entitled: See Attached Schedule

Grandis, Inc.
(Name of Assignee) a Corporation
(Type of Assignee, e.g., corporation, partnership, university, government agency, etc.)

states that it is:

1. ☒ the assignee of the entire right, title, and interest; or
2. ☐ an assignee of less than the entire right, title and interest.
The extent (by percentage) of its ownership interest is _____ %

In the patent application/patent identified above by virtue of either:

- A. ☒ An assignment from the inventor(s) of the patent application/patent identified above. The assignment was in the United States Patent and Trademark Office at Reel See Attached Schedule, Frame See Attached Schedule, or for which a copy thereof is attached.

OR

- B. ☐ A chain of title from the inventor(s), of the patent application/patent identified above, to the current assignee as shown below:

1. From: _____ To: _____
The document was recorded in the United States Patent and Trademark Office at Reel _____, Frame _____, or for which a copy thereof is attached.
2. From: _____ To: _____
The document was recorded in the United States Patent and Trademark Office at Reel _____, Frame _____, or for which a copy thereof is attached.
3. From: _____ To: _____
The document was recorded in the United States Patent and Trademark Office at Reel _____, Frame _____, or for which a copy thereof is attached.

☐ Additional documents in the chain of title are listed on a supplemental sheet.

☐ Copies of assignments or other documents in the chain of title are attached.

(NOTE: A separate copy (i.e., a true copy of the original assignment document(s)) must be submitted to Assignment Division in accordance with 37 CFR Part 3, if the assignment is to be recorded in the records of the USPTO. See MPEP 302.08)

The undersigned (whose title is supplied below) is authorized to act on behalf of the assignee.

Yiming Huai Signature Yiming Huai Date
Printed or Typed Name
Co-Founder, Chief Technology Officer, Vice President of Engineering, Director Title
(408)945-2164 Telephone Number

This collection of information is required by 37 CFR 3.73(b). The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.11 and 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

If you need assistance in completing the form, call 1-800-PTO-6199 and select option 2

Assignment Schedule - 37 CFR 3.73(b) Statement

<u>Atty Docket</u>	<u>Application Serial Number</u>	<u>Assignment Recordation Date</u>	<u>Assignment Reel</u>	<u>Assignment Frame</u>	<u>Title of the Invention</u>
2959P	10/714,357	11/14/2003	014710/0950	014710/0950	STRESS ASSISTED CURRENT DRIVEN SWITCHING FOR MAGNETIC MEMORY APPLICATIONS
3037D	11/685,723	2/19/2004	015012/0907	015012/0907	SPIN TRANSFER MAGNETIC ELEMENT HAVING LOW SATURATION MAGNETIZATION FREE LAYERS
3066C	11/239,969	2/26/2004	015037/0190	015037/0190	SPIN TRANSFER MAGNETIC ELEMENT WITH FREE LAYERS HAVING HIGH PERPENDICULAR ANISOTROPY AND IN-PLAN EQUILIBRIUM MAGNETIZATION
3230C	11/699,160	9/9/2004	015800/0875	015800/0875	MAGNETIC ELEMENTS WITH SPIN ENGINEERED INSERTION LAYERS AND MRAM DEVICES USING THE MAGNETIC ELEMENTS
3352P	11/294,766	2/14/2006	017260/0307	017260/0307	METHOD AND SYSTEM FOR PROVIDING A HIGHLY TEXTURED MAGNETORESISTANCE ELEMENT AND MAGNETIC MEMORY
3557P	11/147,944	6/8/2005	016679/0263	016679/0263	FAST MAGNETIC MEMORY DEVICES UTILIZING SPIN TRANSFER AND MAGNETIC ELEMENTS USED THEREIN
3615P	11/173,087	7/1/2006	016762/0003	016762/0003	MAGNETIC ELEMENTS HAVING A BIAS FIELD AND MAGNETIC MEMORY DEVICES USING THE MAGNETIC ELEMENTS
3628P	11/185,507	7/19/2005	016802/0219	016802/0219	MAGNETIC ELEMENTS HAVING IMPROVED SWITCHING CHARACTERISTICS AND MAGNETIC MEMORY DEVICES USING THE MAGNETIC ELEMENTS

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3667P	11/210,452	8/23/2005	016921/0556	016921/0556	SPIN-TRANSFER SWITCHING MAGNETIC ELEMENTS USING FERRIMAGNETS AND MAGNETIC MEMORIES USING THE MAGNETIC ELEMENTS
3671P	11/217,258	8/31/2005	016949/0502	016949/0502	CURRENT DRIVEN SWITCHING OF MAGNETIC STORAGE CELLS UTILIZING SPIN TRANSFER AND MAGNETIC MEMORIES USING SUCH CELLS
3691P	11/217,524	8/31/2005	016952/0134	016952/0134	CURRENT DRIVEN SWITCHING OF MAGNETIC STORAGE CELLS UTILIZING SPIN TRANSFER AND MAGNETIC MEMORIES USING SUCH CELLS
3709P	11/251,428	10/14/2005	017106/0611	017106/0611	SPIN TRANSFER BASED MAGNETIC STORAGE CELLS UTILIZING GRANULAR FREE LAYERS AND MAGNETIC MEMORIES USING SUCH CELLS
3725P	11/260,778	10/27/2005	017157/0074	017157/0074	Current Driven Switched Magnetic Storage Cells Having Improved Read and Write Margins and Magnetic Memories Using Such Cells
3753P	11/361,267	2/24/2006	017628/0790	017628/0790	CURRENT DRIVEN MEMORY CELLS HAVING ENHANCED CURRENT AND ENHANCED CURRENT SYMMETRY
3846P	11/436,446	5/18/2006	017918/0871	017918/0871	High Density Magnetic Memory Cell Layout for Spin Transfer Torque Magnetic Memories Utilizing Donut Shaped Transistors
3850P	11/446,391	6/1/2006	017966/0906	017966/0906	METHOD AND SYSTEM FOR PROVIDING A MAGNETIC MEMORY STRUCTURE UTILIZING SPIN TRANSFER

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3856CIP	11/736,290	4/17/2007	019173/0247	019173/0247	METHOD AND SYSTEM FOR USING A PULSED FIELD TO ASSIST SPIN TRANSFER INDUCED SWITCHING OF MAGNETIC MEMORY ELEMENTS
3856P	11/487,723	7/17/2006	018066/0826	018066/0826	METHOD AND SYSTEM FOR USING A PULSED FIELD TO ASSIST SPIN TRANSFER INDUCED SWITCHING OF MAGNETIC MEMORY ELEMENTS
3861P	11/476,171	6/26/2006	018055/0480	018055/0480	Current Driven Switching of Magnetic Storage Cells Utilizing Spin Transfer and Magnetic Memories Using Such Cells Having Enhanced Read and Write Margins
3887CIP	11/523,872	9/20/2006	018324/0242	018324/0242	MAGNETIC ELEMENT UTILIZING FREE LAYER ENGINEERING
3887P	11/487,552	7/14/2006	018065/0608	018065/0608	MAGNETIC ELEMENT UTILIZING FREE LAYER ENGINEERING
3958P	11/589,347	10/30/2006	018475/0918	018475/0918	METHOD AND SYSTEM FOR PROVIDING A CONTACT TO A MAGNETIC ELEMENT IN A MEMORY
4025P	11/692,090	3/27/2007	019072/0475	019072/0475	METHOD AND SYSTEM FOR PROVIDING FIELD BIASED MAGNETIC MEMORY DEVICES
4090P	11/695,614	4/3/2007	019104/0377	019104/0377	METHOD AND SYSTEM FOR PROVIDING DOMAIN WALL ASSISTED SWITCHING OF MAGNETIC ELEMENTS AND MAGNETIC MEMORIES USING SUCH MAGNETIC ELEMENTS
2929P	10/839,064	5/5/2004	015305/0945	015305/0945	MAGNETORESISTIVE ELEMENT HAVING REDUCED SPIN TRANSFER INDUCED NOISE

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2990D	11/413,744	12/22/2003	014851/0081	014851/0081	Magnetic Elements with Ballistic Magnetoresistance Utilizing Spin-Transfer and an MRAM Device Using Such Magnetic Elements
3008C	11/256,387	10/09/2003	013391/0068	013391/0068	Magnetic Element Utilizing Spin-Transfer and Half-Metals and an MRAM Device Using the Magnetic Element
3037P	10/783,416	2/19/2004	015012/0907	015012/0907	SPIN TRANSFER MAGNETIC ELEMENT HAVING LOW SATURATION MAGNETIZATION FREE LAYERS
3095P	10/829,313	4/21/2004	015252/0135	015252/0135	SPIN TRANSFER MAGNETIC ELEMENTS WITH SPIN DEPOLARIZATION LAYERS
3230P	10/938,219	9/9/2004	015800/0875	015800/0875	MAGNETIC ELEMENTS WITH SPIN ENGINEERED INSERTION LAYERS AND MRAM DEVICES USING THE MAGNETIC ELEMENTS
3399P	11/027,397	12/29/2004	016141/0544	016141/0544	MTJ ELEMENTS WITH HIGH SPIN POLARIZATION LAYERS CONFIGURED FOR SPIN-TRANSFER SWITCHING AND SPINTRONICS DEVICES USING THE MAGNETIC ELEMENTS
3648P	11/192,811	7/29/2005	016834/0181	016834/0181	MAGNETIC DEVICES HAVING A HARD BIAS FIELD AND MAGNETIC MEMORY DEVICES USING THE MAGNETIC DEVICES